



ZXTP2013G

100V PNP MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

Features

- BV_{CEO} > -100V
- I_C = -5A High Continuous Collector Current
- I_{CM} = -10A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < -90mV @ -1A
- $R_{SAT} = 60m\Omega$ for a Low Equivalent On-Resistance
- h_{FE} Specified Up to -10A for a High Gain Hold-Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 (e3)
- Weight: 0.112 grams (Approximate)

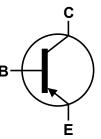
Application

- Motor Driving
- Line Switching
- High Side Switches
- Subscriber Line Interface Cards (SLIC)

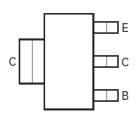




Top View



Device Symbol



Top View Pin-Out

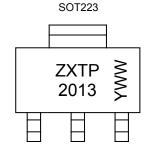
Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXTP2013GTA	AEC-Q101	ZXTP2013	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



ZXTP2013 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 1= 2021) WW or $\overline{W}W$ = Week Code (01~53)



Absolute Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-140	V
Collector-Emitter Voltage	V _{CEO}	-100	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	Ic	-5	Α
Peak Pulse Current	Ісм	-10	А

Thermal Characteristics (@ TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5) Linear Derating Factor	P _D	3.0 24	W mW/°C
Power Dissipation (Note 6) Linear Derating Factor	P _D	1.6 12.8	W mW/°C
Thermal Resistance, Junction to Ambient (Note 5)	R _{0JA}	42	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	78	°C/W
Thermal Resistance Junction to Lead (Note 7)	R _{0JL}	10.48	°C/W
Thermal Resistance Junction to Case (Note 8)	Rejc	13.8	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C

ESD Ratings (Note 9)

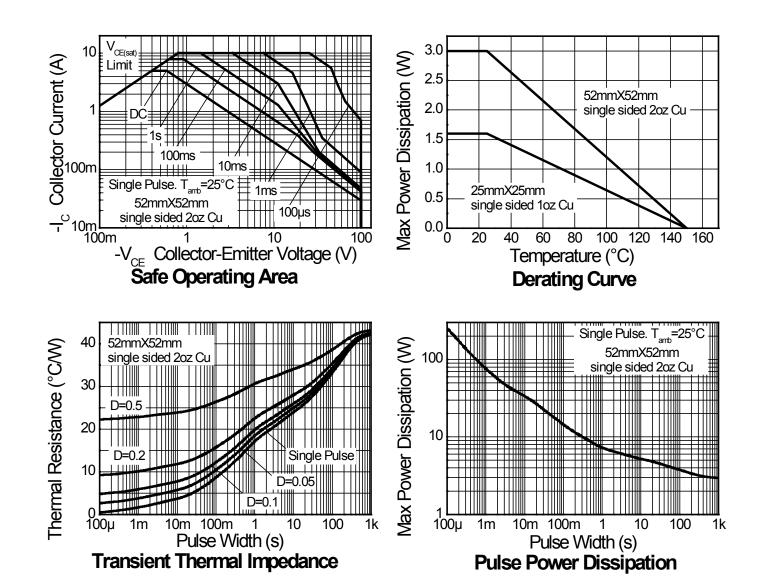
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under For a device mounted with the collector lead on 52mm x 52mm 202 copper that is still air conditions whilst operating in steady-state.
 Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 Thermal resistance from junction to solder-point (at the end of the collector lead).
 Thermal resistance from junction to top of the case.
 Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information





Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

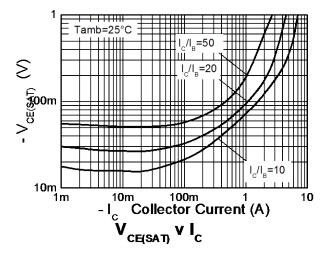
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-140	-160	_	V	I _C = -100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CER}	-140	-160	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV _{CEO}	-100	-115	_	V	I _C = -1mA
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.1	_	V	I _E = -100μA
Collector Cut-Off Current	I _{CBO}	_	< 1 —	-20 -500	nA nA	V _{CB} = -100V V _{CB} = -100V, T _A = +100°C
Collector Cut-Off Current	I _{CER} R≤1kΩ	_ _	< 1 —	-20 -500	nA nA	V _{CB} = -100V V _{CB} = -100V, T _A = +100°C
Emitter Cut-Off Current	I _{EBO}	_	< 1	-10	nA	V _{EB} = -6V
		100	250	_		I _C = -10mA, V _{CE} = -1V
		100	200	300		I _C = -1A, V _{CE} = -1V
DC Current Transfer Static Ratio (Note 10)	h _{FE}	25	50	_		I _C = -3A, V _{CE} = -1V
		15	30	_		I _C = -4A, V _{CE} = -1V
		_	5	_		$I_C = -10A$, $V_{CE} = -1V$
	V _{CE} (sat)	_	-20	-30	mV	I _C = -100mA, I _B = -10mA
Collector-Emitter Saturation Voltage (Note 10)		_	-70	-90		$I_C = -1A$, $I_B = -100mA$
Collector-Entitler Saturation Voltage (Note 10)		_	-120	-150		$I_C = -2A$, $I_B = -200mA$
		_	-240	-340		$I_C = -4A$, $I_B = -400mA$
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(sat)}$	_	-985	-1100	mV	$I_C = -4A$, $I_B = -400mA$
Base-Emitter Turn-On Voltage (Note 10)	V _{BE(on)}	_	-920	-1050	mV	$I_C = -4A$, $V_{CE} = -1V$
Transitional Frequency (Note 10)	f⊤	_	125	_	MHz	I _C = -100mA, V _{CE} = -10V, f = 50MHz
Output Capacitance	C_{obo}	_	42	_	pF	V _{CB} = -10V, f = 1MHz
Switching Time	t _{on}	_	42	_	ns	$V_{CC} = -50V, I_{C} = -1A,$
Switching Time	t _{off}	_	540	_	115	$I_{B1} = -I_{B2} = -100 \text{mA}$

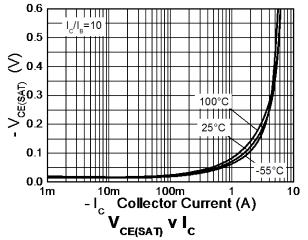
Note:

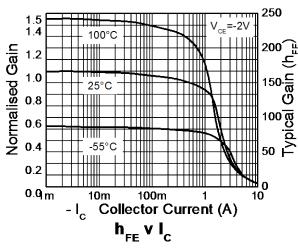
10. Measured under pulsed conditions. Pulse width \leq 300µs. Duty cycle \leq 2%.

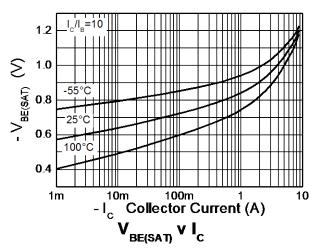


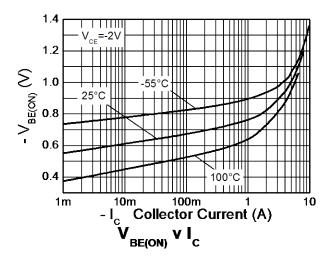
Typical Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)









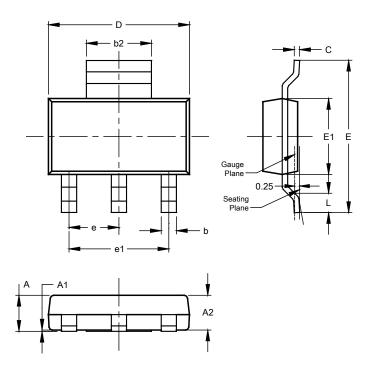




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)

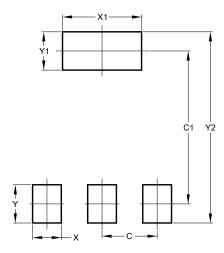


SOT223 (Type DN)				
Dim	Min	Max	Тур	
Α		1.70		
A1	0.01	0.15		
A2	1.50	1.68	1.60	
b	0.60	0.80	0.70	
b2	2.90	3.10		
С	0.20	0.32		
D	6.30	6.70		
Е	6.70	7.30		
E1	3.30	3.70		
е	-		2.30	
e1			4.60	
L	0.85			
All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT223 (Type DN)



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00



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